

MBRF10H150CTG

Switch-mode Power Rectifier 150 V, 10 A

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capability
- 10 A Total (5 A Per Diode Leg)
- Guard-Ring for Stress Protection
- This is a Pb-Free Device

Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes:
260°C Max. for 10 Seconds

MAXIMUM RATINGS

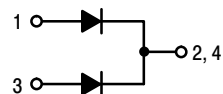
Please See the Table on the Following Page



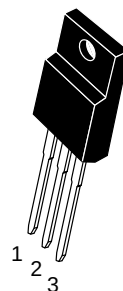
ON Semiconductor®

www.onsemi.com

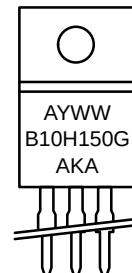
SCHOTTKY BARRIER RECTIFIER 10 AMPERES, 150 VOLTS



MARKING DIAGRAM



TO-220 FULLPAK™
CASE 221AH



A = Assembly Location
Y = Year
WW = Work Week
B10H150 = Device Code
G = Pb-Free Device
AKA = Polarity Designator

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MBRF10H150CTG

MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	150	V
Average Rectified Forward Current (Per Leg) (Rated V_R) $T_C = 142^\circ\text{C}$ (Per Device)	$I_{F(AV)}$	5 10	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150	A
Operating Junction Temperature (Note 1)	T_J	-20 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	10000	V/ μs
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum Thermal Resistance – Junction-to-Case	$R_{\theta JC}$	2.5	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Rating	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($I_F = 5\text{ A}$, $T_C = 25^\circ\text{C}$) ($I_F = 5\text{ A}$, $T_C = 125^\circ\text{C}$)	V_F	0.85 0.63	0.69	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_C = 25^\circ\text{C}$) (Rated DC Voltage, $T_C = 125^\circ\text{C}$)	I_R		45 20	μA mA

2. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

DEVICE ORDERING INFORMATION

Device Order Number	Package Type	Shipping [†]
MBRF10H150CTG	TO-220FP (Pb-Free)	50 Units / Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MBRF10H150CTG

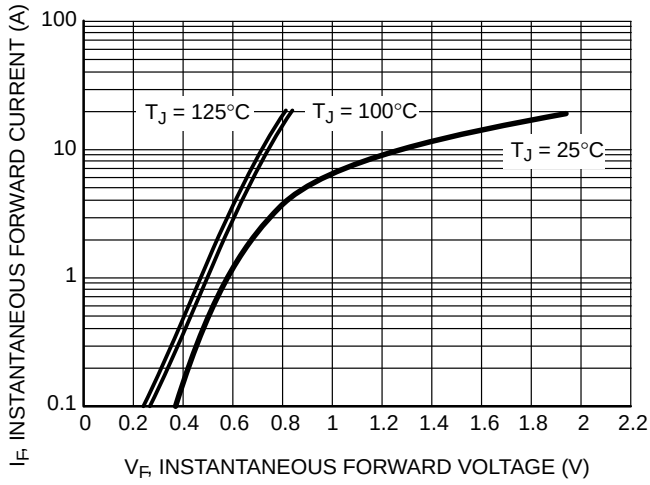


Figure 1. Typical Forward Voltage

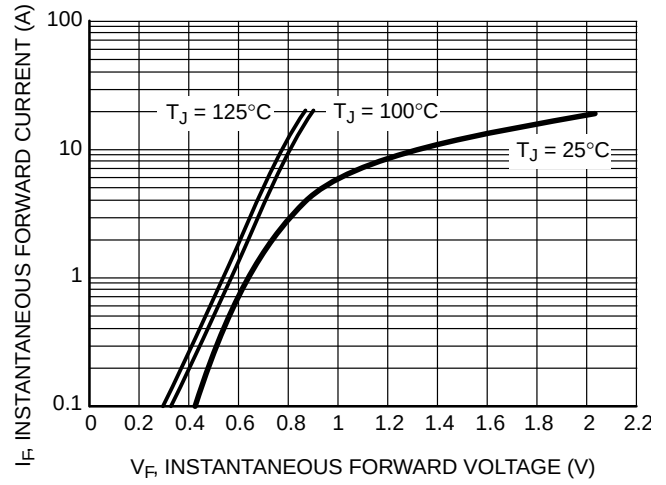


Figure 2. Maximum Forward Voltage

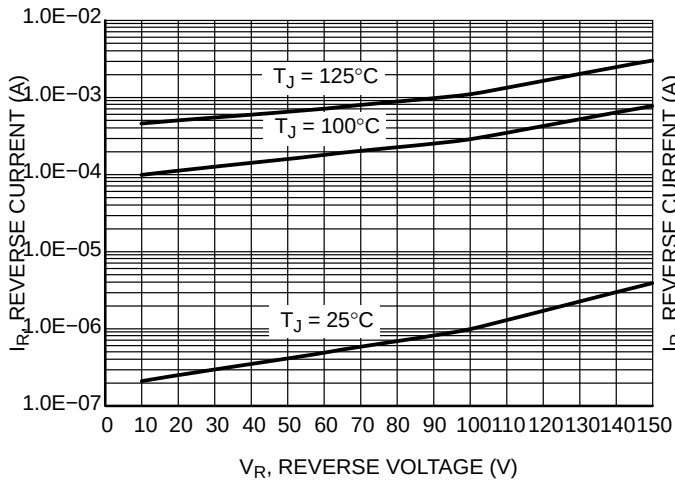


Figure 3. Typical Reverse Current

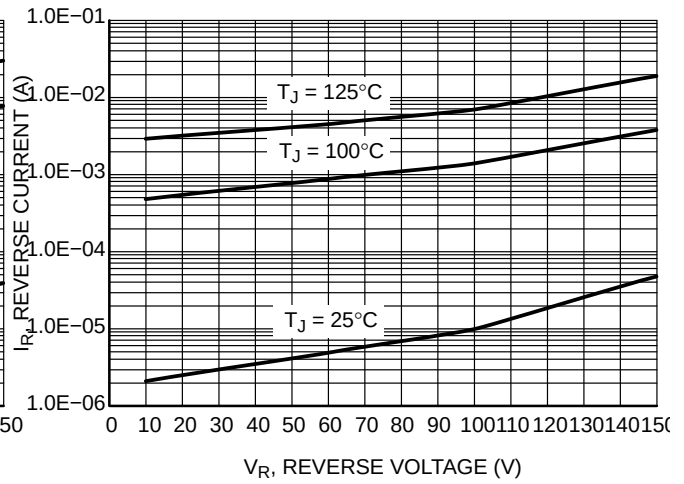


Figure 4. Maximum Reverse Current

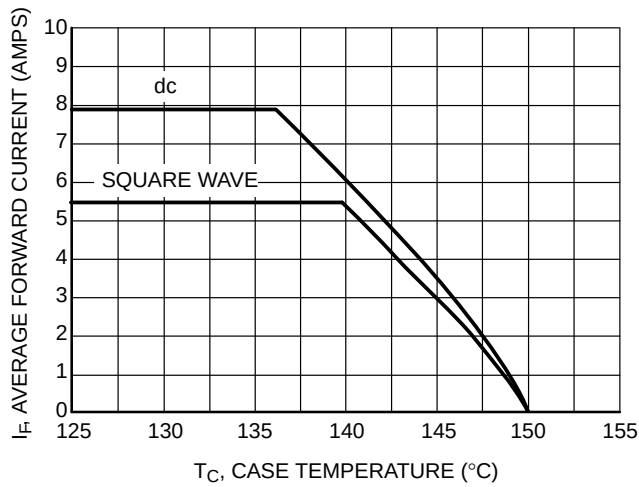


Figure 5. Current Derating

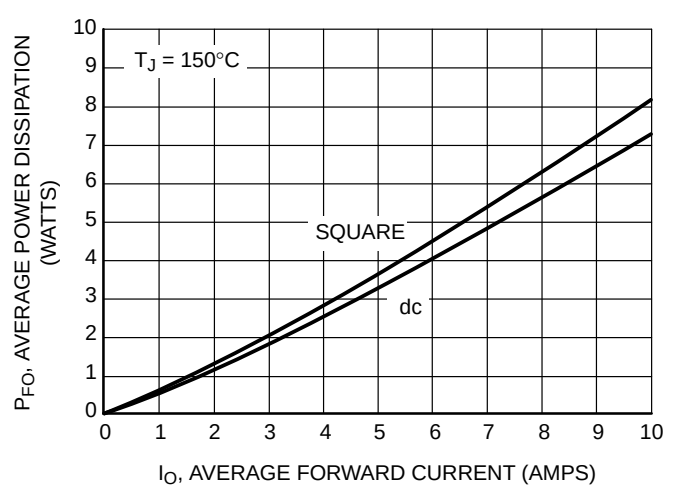


Figure 6. Forward Power Dissipation

MBRF10H150CTG

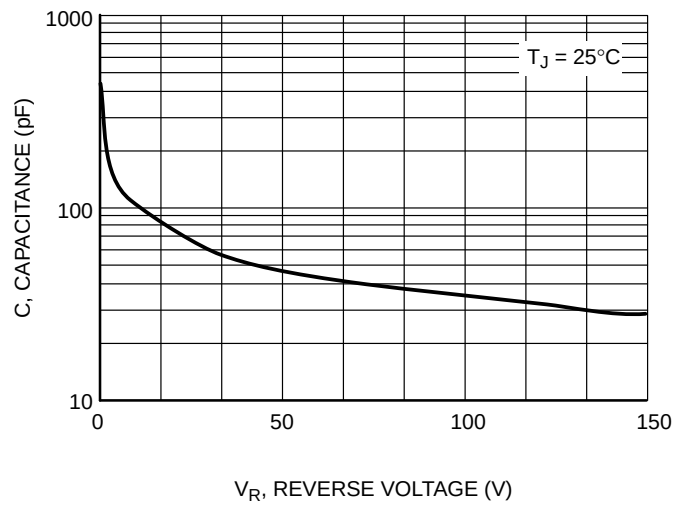


Figure 7. Capacitance

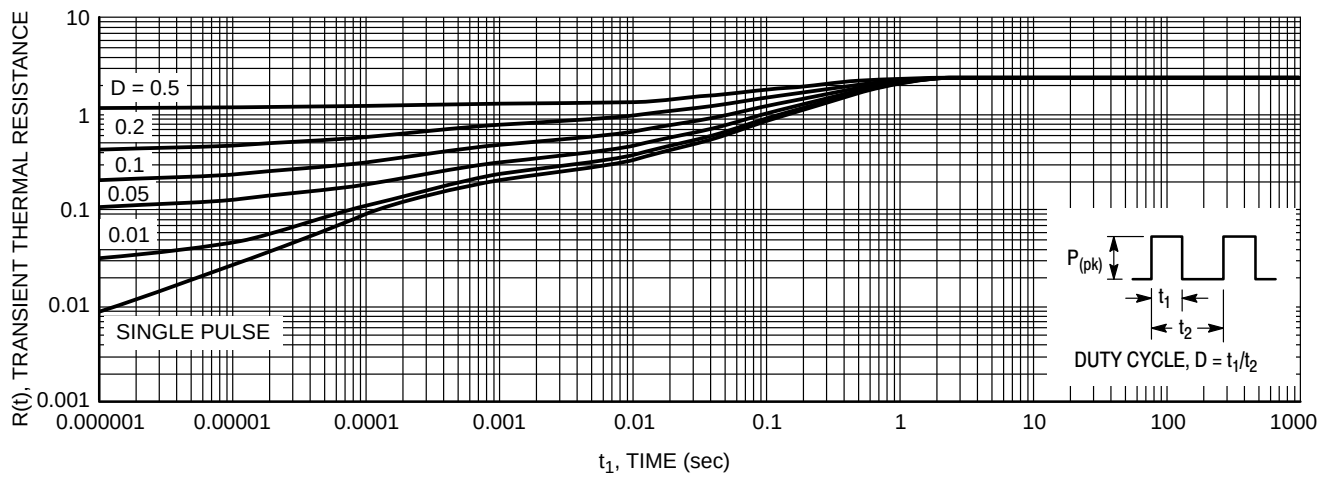


Figure 8. Thermal Response Junction-to-Case for MBRF10H150CTG

